NSN 5961-01-417-6572

Diode Semiconductor Device - Page 1 of 1

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Inclosure Material:

Ceramic and metal

Overall Length:

Between 0.130 inches and 0.146 inches

Overall Diameter:

Between 0.063 inches and 0.067 inches

Mounting Method:

Press fit

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

6.8 regulator voltage

Voltage Tolerance In Percent:

-5.0/+5.0

Current Rating Per Characteristic:

60.00 milliamperes repetitive peak forward current

Power Rating Per Characteristic:

500.0 milliwatts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

175.0 degrees celsius ambient air

Test Data Document:

81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

2 case

Specification Data:

81349-mil-s-19500/127 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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